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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)

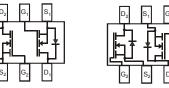


TOP VIEW

SOT-563

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



DMN5L06V (KAH Marking Code) (K

DMN5L06VA (KAG Marking Code)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characterist	ic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	50	V	
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ		V_{DGR}	50	V	
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V	
Drain Current (Note 1)	Continuous	I _D	280	mA	
Drain Current (Note 1)	Pulsed	I _{DM}	1.5	A	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

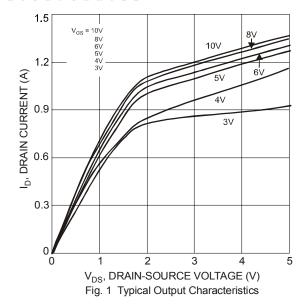
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	qvT	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}	_	_	0.1 500	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		$V_{GS(th)}$	0.49		1.2	>	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		R _{DS} (ON)		1.6 2.2	3 4	Ω	$V_{GS} = 2.7V$, $I_D = 0.2A$, $V_{GS} = 1.8V$, $I_D = 50mA$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		Y _{fs}	200	_	_	mS	V _{DS} =10V, I _D = 0.2A
Source-Drain Diode Forward Voltage		V_{SD}	0.5	_	1.4	V	V _{GS} = 0V _, I _S = 115mA
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_		50	рF	
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}	_	_	5.0	pF	

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead.
- 3. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 4. Short duration pulse test used to minimize self-heating effect.





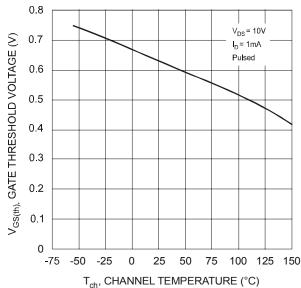
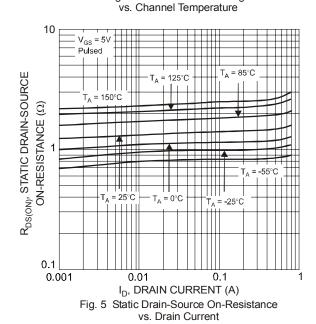


Fig. 3 Gate Threshold Voltage



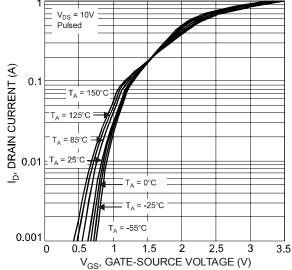


Fig. 2 Typical Transfer Characteristics

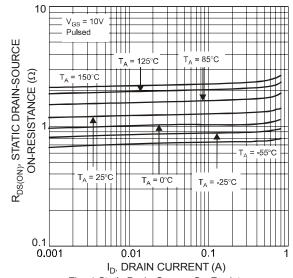


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

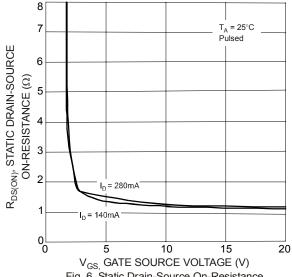


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



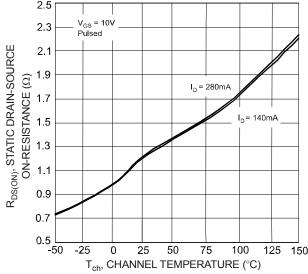
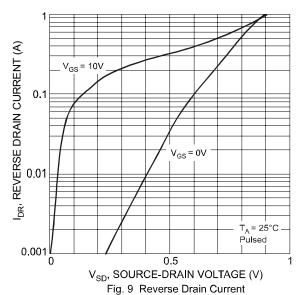
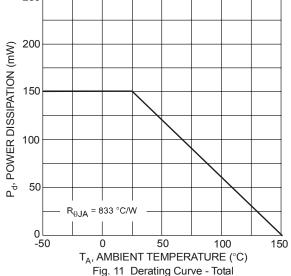


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature



250 200

vs. Source-Drain Voltage



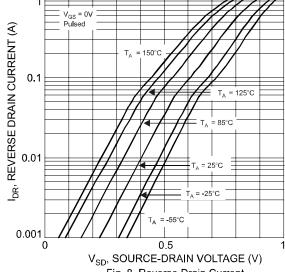


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

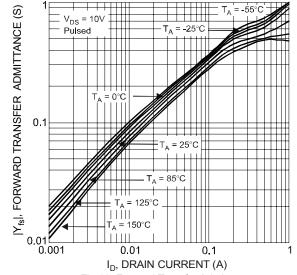


Fig. 10 Forward Transfer Admittance vs. Drain Current

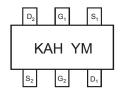


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN5L06V-7	SOT-563	3000/Tape & Reel
DMN5L06VA-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information (Note 6)



KAH = DMN5L06V Product Type Marking Code (See Note 6) YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September



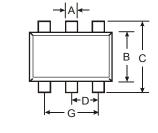
KAG = DMN5L06VA Product Type Marking Code(See Note 6) YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September

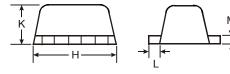
Notes: 6. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Date Code Kev

Year	2005		2006	2007		2008	2009)	2010	2011		2012
Code	S		T	U		V	W		Χ	Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4	_	•	4	-	6	7	0	0	^	N.I.	7

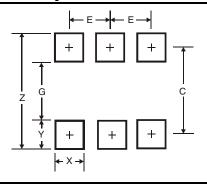
Package Outline Dimensions





SOT-563						
Dim	Min Max Typ					
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55 1.70 1.60					
D	0.50					
G	0.90 1.10 1.00					
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
١	0.10	0.30	0.20			
М	0.10	0.18	0.11			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Υ	0.5
С	1.7
E	0.5

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